Process Flow

1. silicon substrate
2. deposit pecvd oxide (~237nm)
   - STS PECVD, std ox, hi freq
3. coat ZEP520 (~400nm)
4. etch oxide, STS AOE (recipe = dkb_ox.set)
   - 4 mTorr, 55sccm He, 22sccm CF4, 5 sccm C4F8, 400W coil, 200W plate, 30 sec

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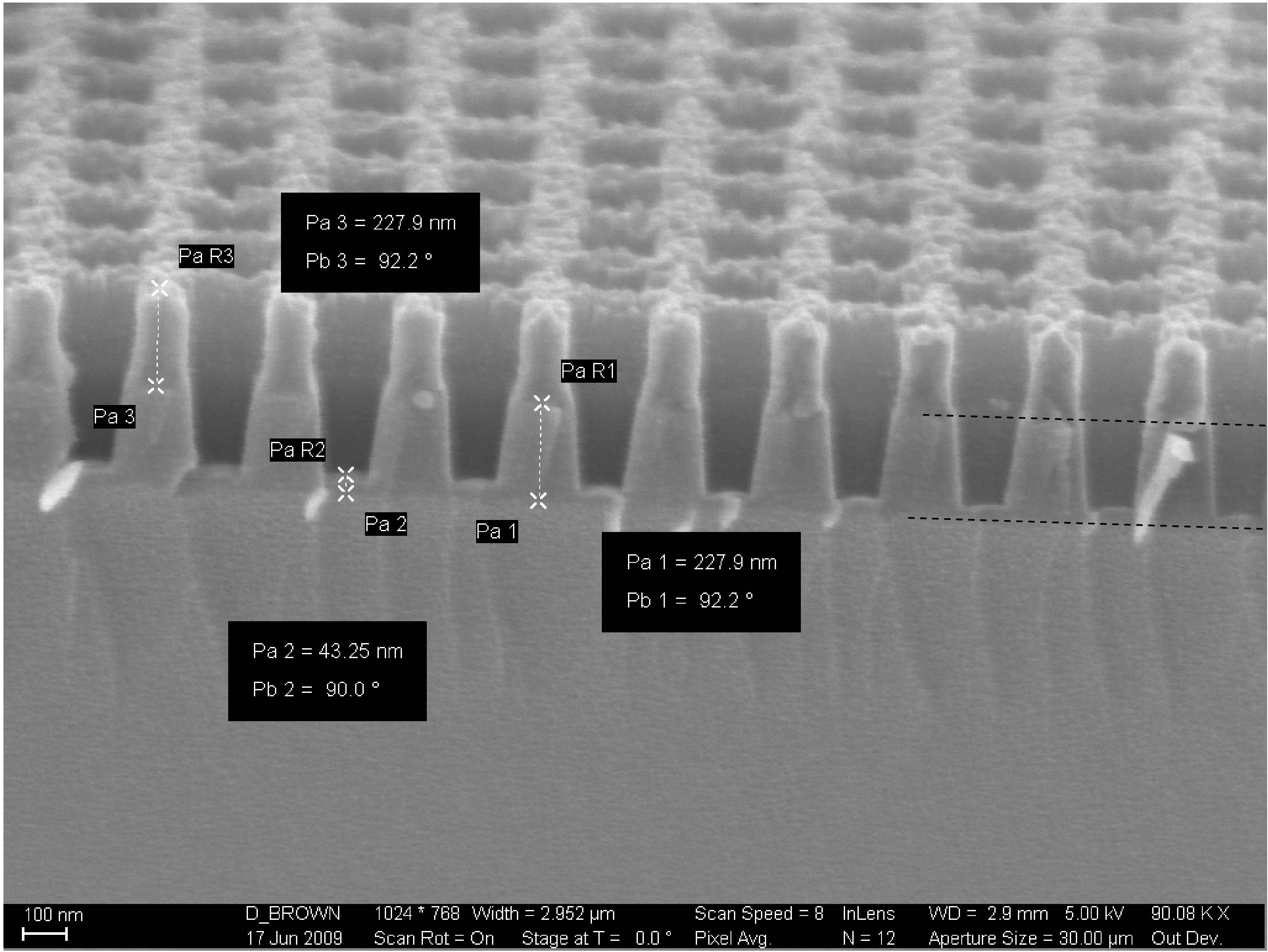
STS AOE oxide etch after 30sec



ZEP520

oxide

silicon

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oxide etch rate = (228 – 43nm) / (30sec) = 6.2nm/sec

resist etch rate = (400 – 228nm) / (30sec) = 5.7nm/sec

selectivity (oxide:ZEP520) = 6.2/5.7 = 1.1

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